



PATENT APPLICATION

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Makoto IIDA et al.

Application No.: 09/869,912

Filed: July 9, 2001

For: SILICON SINGLE CRYSTAL WAFER AND PRODUCTION METHOD THEREOF
AND SOI WAFER

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Examiner: R. M. Kunemund

Docket No.: 110051

AMENDMENT

Fee Paid

Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

In reply to the January 29, 2003 Office Action, please amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claims 13-16 and 25 as follows:

13. (Amended) A silicon single crystal wafer grown by the Czochralski method, which is doped with nitrogen, and has an N-region for the entire plane and an interstitial oxygen concentration of 5-8 ppma.

14. (Amended) A silicon single crystal wafer grown by the Czochralski method, which is doped with nitrogen, and has an interstitial oxygen concentration of 5-8 ppma, and in which at least void type defects and dislocation clusters are eliminated from the entire plane.

15. (Amended) A silicon single crystal wafer, which is doped with nitrogen, has an N-region for the entire plane, and has an interstitial oxygen concentration of 5 ppma or less, and one main surface of the silicon single crystal wafer is subjected to an EG treatment.

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